

MDD06N03J

30V N-Channel Enhancement Mode MOSFET

1. Description

This N-Channel MOSFET is produced using MDD Semiconductor's advanced Power Trench process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

2. Features

- Max $R_{DS(on)}$ = 21 m Ω at V_{GS} = 10 V, I_D = 5 A
- Extremely Low Reverse Recovery Charge, Q_{rr}
- 100% UIS Tested
- RoHS Compliant

3. Application

- DC to DC conversion
- Low-side load switch
- Battery management
- Switching circuits

4. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	6	A
Pulsed Drain Current (Note 2)	I_{DM}	24	A
Thermal Resistance, steady-state	$R_{\theta JA}$	50	$^{\circ}\text{C}/\text{W}$
Power Dissipation	P_D	2.5	W
Junction Temperature	T_J	$-55 \sim +150$	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	$-55 \sim +150$	$^{\circ}\text{C}$

Note: 1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating, pulse width limited by max. junction temperature.

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Equivalent Circuit	Marking	Package
3	G	Gate			06N03J XXY: Date code	DFN2020 - 6L
1-2, 5-6	D	Drain				
4	S	Source				

6. $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter		Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		$V_{GS}=0V, I_D=250\mu A$	30	—	—	V
I_{SS}	Gate-Source Leakage Current	Forward	$V_{GS}=20V$	—	—	100	nA
		Reverse	$V_{GS}=-20V$	—	—	-100	nA
I_{DSS}	Drain-Source Leakage Current		$V_{DS}=30V, V_{GS}=0V$	—	—	1	μA
$V_{GS(TH)}$	Gate Threshold Voltage		$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance		$V_{GS}=10V, I_D=5A$	—	14	21	m Ω
			$V_{GS}=4.5V, I_D=3A$	—	21	32	m Ω

7. Dynamic Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS}=0V$	—	460	—	pF
C_{oss}	Output Capacitance	$V_{DS}=15V$	—	85	—	pF
C_{rss}	Reverse Transfer Capacitance	$f=1MHz$	—	60	—	pF
Q_g	Total Gate Charge	$V_{GS}=10V$	—	10	—	nC
Q_{gs}	Gate Source Charge	$V_{DS}=30V$	—	2.3	—	nC
Q_{gd}	Gate Drain Charge	$I_D=5A$	—	2.5	—	nC

8. Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{d(on)}$	Turn on Delay Time	$V_{GS}=10V$ $V_{DD}=15V$ $I_D=5A$ $R_G=3\Omega$	—	5	—	ns
t_r	Turn on Rise Time		—	25	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	15	—	ns
t_f	Turn Off Fall Time		—	3.5	—	ns

9. Source Drain Diode Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{SD}	Drain-Source Diode Forward Voltage	$I_S=5A, V_{GS}=0V$	—	0.8	—	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5A$	—	6	—	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$di/dt=100A/\mu s$	—	1.5	—	nC

10. Test Circuits And Waveforms

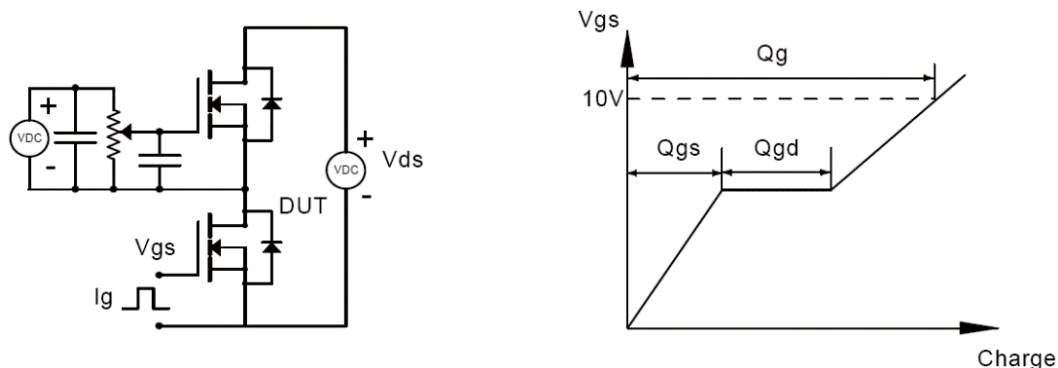


Figure 1. Gate charge test circuit & waveform

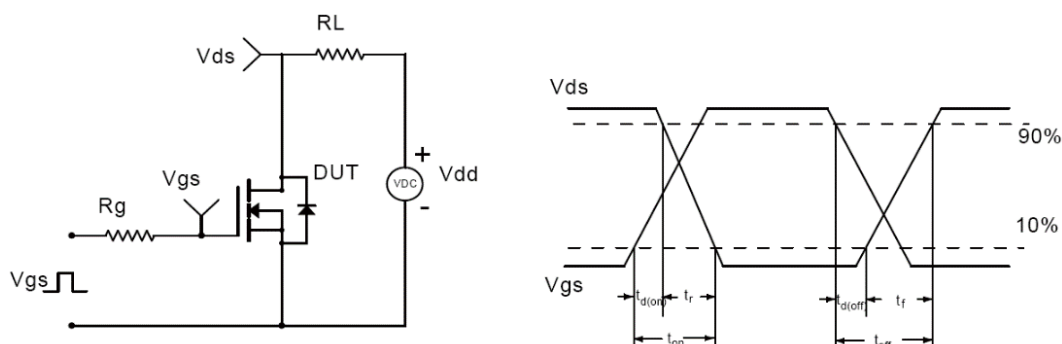


Figure 2. Switching time test circuit & waveforms

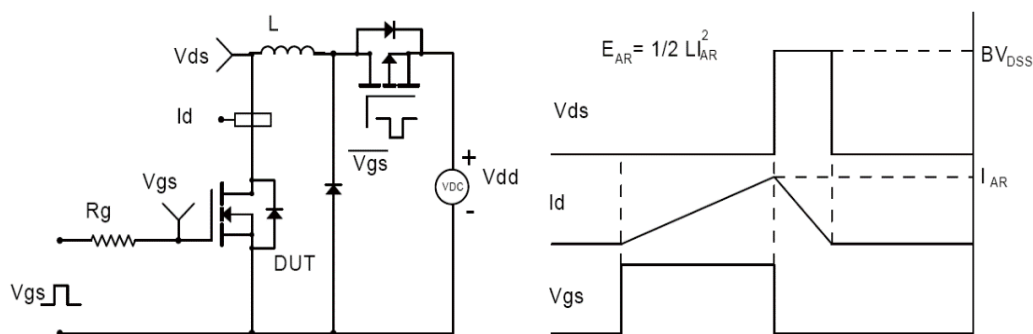


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

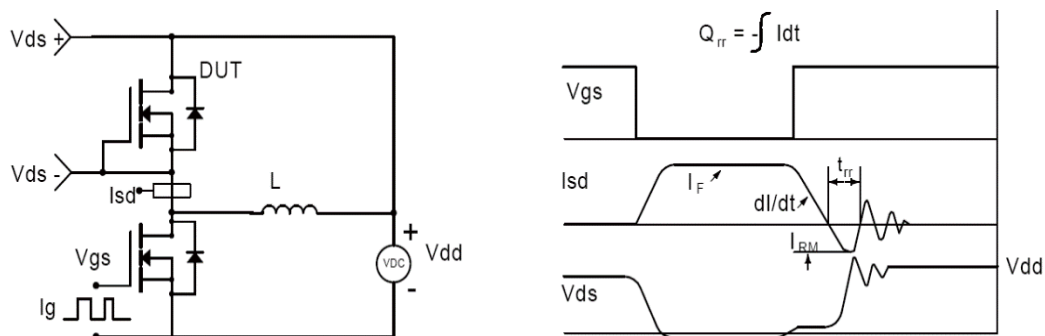


Figure 4. Diode reverse recovery test circuit & waveforms

11. Electrical Characteristics Diagrams

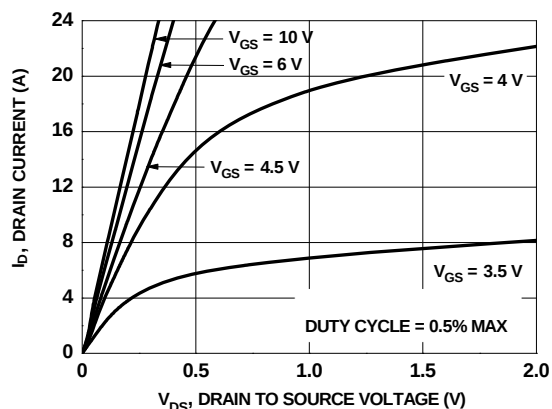


Figure 1. Typ. output characteristics

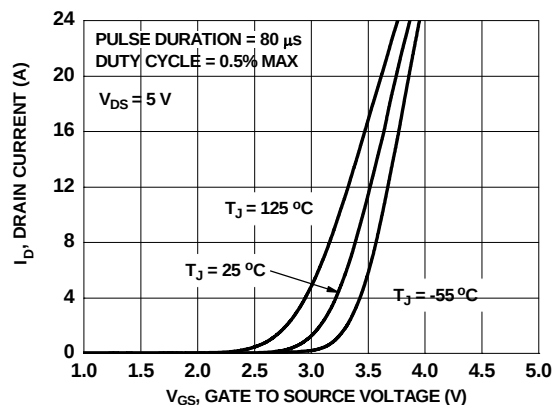


Figure 2. Typ. transfer characteristics

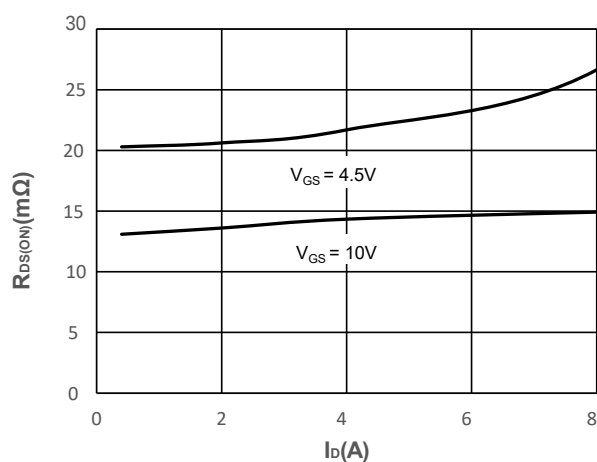


Figure 3. On-Resistance vs. Drain Current

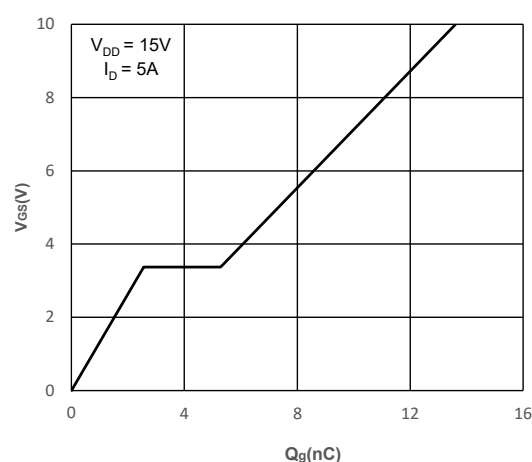


Figure 4. Gate Charge Characteristics

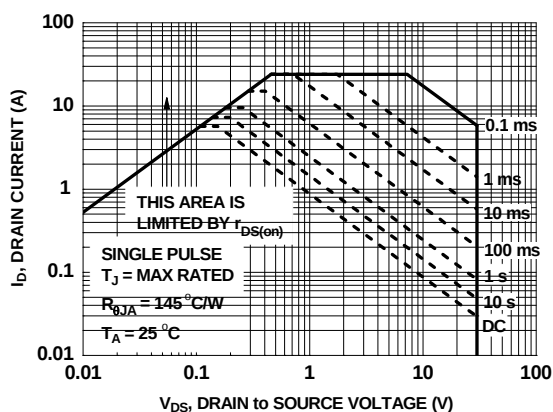


Figure 5. Maximum Safe Operating Area

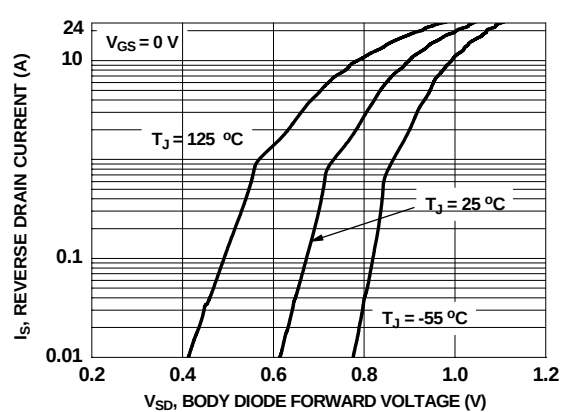
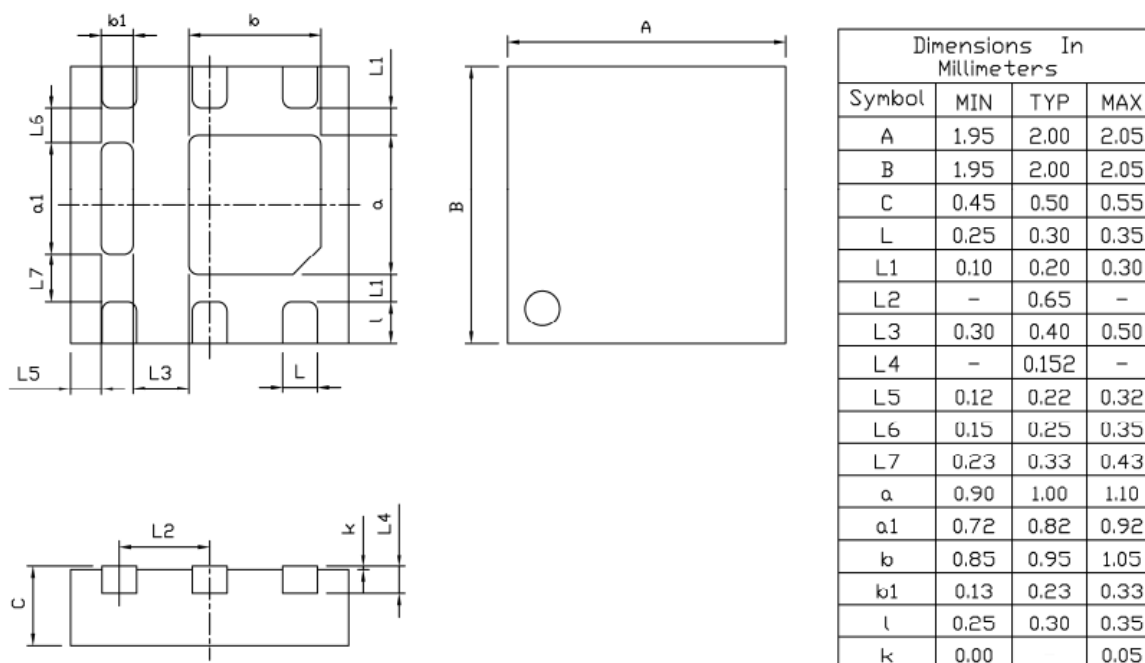


Figure 6. Forward characteristic of body diode

12. Outline Drawing

DFN2020 - 6L Package Outline Dimensions



13. Important Notice and Disclaimer

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